

ABSTRACT

The present invention relates to a method for developing a photoresist pattern. The method consists of mixing a concentrated chemical solution with a solvent to obtain a diluted chemical solution of a predetermined concentration. In this method, the mixing is done in a fabrication facility where the substrates are processed. The diluted chemical solution is then applied onto the photoresist pattern. Analysis of the pattern is then carried out to detect any defects or pattern collapse on the substrate. In the event that defects and/or pattern collapse occur, the predetermined concentration is adjusted to reduce the phenomenon.